

Application No. Applicant(s) 10/643.970 ARIYOSHI ET AL. Notice of Allowability Examiner Art Unit Trung Dang 2823 -- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308. 1. This communication is responsive to _____. 2. The allowed claim(s) is/are 1-13. 3. The drawings filed on are accepted by the Examiner. 4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) 🛛 All b) Some* c) None 1. \(\subseteq \text{ Certified copies of the priority documents have been received.} \) 2. Certified copies of the priority documents have been received in Application No. 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)). * Certified copies not received: _ Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient. 6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached 1) Thereto or 2) to Paper No./Mail Date _____. (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). 7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. Attachment(s) 1. Notice of References Cited (PTO-892) 5. Notice of Informal Patent Application (PTO-152) Interview Summary (PTO-413). 2. Notice of Draftperson's Patent Drawing Review (PTO-948) Paper No./Mail Date 7. X Examiner's Amendment/Comment 3. Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No./Mail Date 8/20/03 4. Examiner's Comment Regarding Requirement for Deposit 8. X Examiner's Statement of Reasons for Allowance of Biological Material 9. ☐ Other .

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Stephen G. Adrian on 09/17/04.

IN THE CLAIMS

Claim 1, line 22, change "second" to --first--; line 24, change "a" to --an--.

Allowable Subject Matter

2. The following is an examiner's statement of reasons for allowance:

Independent claim 1 and its dependent claims are allowed over the prior art of record because the prior art does not teach or suggest the claimed semiconductor device, which includes the structure of: an opening formed in a first insulation layer exposing part of a low concentration impurity below; a source/drain layer formed at a position aligned with the opening; a second insulation layer covering the gate electrode and the first insulation layer; and a contact hole formed in a width larger

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than that of the opening at a position aligned with the opening in the first insulation layer, the contact hole reaching the source/drain layer from an upper surface of the second insulation layer via the opening.

Independent claim 7 and its dependent claims are allowed over the prior art of record because the prior art does not teach or suggest the claimed semiconductor device, which includes the structure of: a first insulation layer formed on the low concentration impurity layer and the gate electrode; an opening in the first insulation layer exposing part of the gate electrode; a silicide film on the surface of the gate electrode inside said opening; a second insulation layer covering the gate electrode and the first insulation layer; a contact hole reaching the low concentration layer from an upper surface of the second insulation layer; and a source/drain layer formed in the low concentration impurity layer at a position aligned with the contact hole.

All method claims are allowed because they includes process steps that correspond to every element of the structure of either claim 1 or 7.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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3. Any inquiry concerning this communication or earlier communications from

the examiner should be directed to Trung Dang whose telephone number is 571-

272-1857. The examiner can normally be reached on Mon-Friday 9:30am-6:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the

examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax

phone number for the organization where this application or proceeding is assigned

is 703-872-9306.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for

published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR

only. For more information about the PAIR system, see http://pair-direct.uspto.gov.

Should you have questions on access to the Private PAIR system, contact the

Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Trung Dang Primary Examiner

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